

BZX79C2V4RL Series

500 mW DO-35 Hermetically Sealed Glass Zener Voltage Regulators

This is a complete series of 500 mW Zener diodes with limits and excellent operating characteristics that reflect the superior capabilities of silicon-oxide passivated junctions. All this in an axial-lead hermetically sealed glass package that offers protection in all common environmental conditions.

Specification Features:

- Zener Voltage Range – 2.4 V to 33 V
- ESD Rating of Class 3 (>16 KV) per Human Body Model
- DO-204AH (DO-35) Package – Smaller than Conventional DO-204AA Package
- Double Slug Type Construction
- Metallurgical Bonded Construction

Mechanical Characteristics:

CASE: Double slug type, hermetically sealed glass

FINISH: All external surfaces are corrosion resistant and leads are readily solderable

MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 230°C, 1/16" from the case for 10 seconds

POLARITY: Cathode indicated by polarity band

MOUNTING POSITION: Any

MAXIMUM RATINGS (Note 1.)

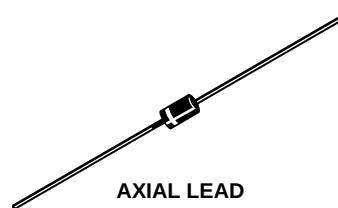
Rating	Symbol	Value	Unit
Max. Steady State Power Dissipation @ $T_L \leq 75^\circ\text{C}$, Lead Length = 3/8" Derate above 75°C	P_D	500 4.0	mW mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	-65 to +200	°C

1. Some part number series have lower JEDEC registered ratings.



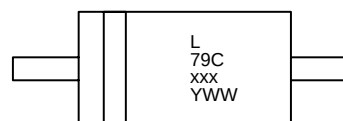
ON Semiconductor™

<http://onsemi.com>



AXIAL LEAD
CASE 299
GLASS

MARKING DIAGRAM



L = Assembly Location
79Cxxx = Device Code
(See Table Next Page)
Y = Year
WW = Work Week

ORDERING INFORMATION

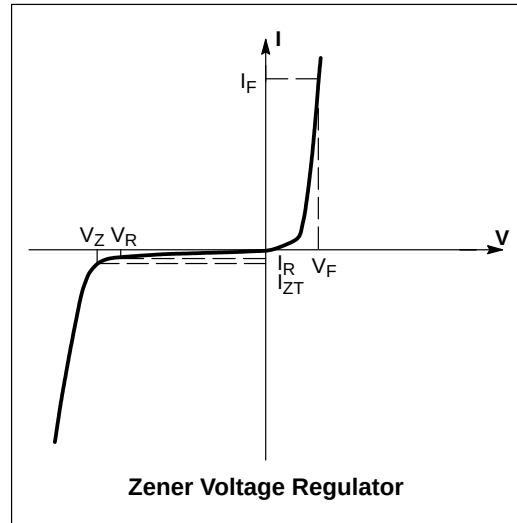
Device	Package	Shipping
BZX79CxxxRL	Axial Lead	5000/Tape & Reel
BZX79CxxxRL2*	Axial Lead	5000/Tape & Reel

* The "2" suffix refers to 26 mm tape spacing.

BZX79C2V4RL Series

ELECTRICAL CHARACTERISTICS ($T_L = 30^\circ\text{C}$ unless otherwise noted, $V_F = 1.5\text{ V Max}$ @ $I_F = 100\text{ mA}$ for all types)

Symbol	Parameter
V_Z	Reverse Zener Voltage @ I_{ZT}
I_{ZT}	Reverse Current
Z_{ZT}	Maximum Zener Impedance @ I_{ZT}
ΘV_{BR}	Temperature Coefficient of V_{BR} (Typical)
I_R	Reverse Leakage Current ($T_A = 25^\circ\text{C}$) @ V_R
V_R	Breakdown Voltage
I_F	Forward Current
V_F	Forward Voltage @ I_F
C	Capacitance (Typical)



ELECTRICAL CHARACTERISTICS ($T_L = 30^\circ\text{C}$ unless otherwise noted, $V_F = 1.5\text{ V Max}$ @ $I_F = 100\text{ mA}$ for all types)

Device (Note 2.)	Device Marking	Zener Voltage (Note 3.)				Z _{ZT} (Note 4.) @ I _{ZT} (f = 1.0 kHz)	Leakage Current		ΘV _{BR}		C V _Z = 0, f = 1.0 MHz
		V _Z (Volts)			@ I _{ZT}		I _R @ V _R		mV/°C		
		Min	Nom	Max			mA	Ω	μA	Volts	
BZX79C2V4RL	79C2V4	2.28	2.4	2.52	5	100	100	1	−3.5	0	255
BZX79C2V7RL	79C2V7	2.57	2.7	2.84	5	100	75	1	−3.5	0	230
BZX79C3V0RL	79C3V0	2.85	3.0	3.15	5	95	50	1	−3.5	0	215
BZX79C3V3RL	79C3V3	3.14	3.3	3.47	5	95	25	1	−3.5	0	200
BZX79C3V6RL	79C3V6	3.42	3.6	3.78	5	90	15	1	−3.5	0	185
BZX79C3V9RL	79C3V9	3.71	3.9	4.10	5	90	10	1	−3.5	0.3	175
BZX79C4V7RL	79C4V7	4.47	4.7	4.94	5	80	3	2	−3.5	0.2	130
BZX79C5V1RL	79C5V1	4.85	5.1	5.36	5	60	2	2	−2.7	1.2	110
BZX79C5V6RL	79C5V6	5.32	5.6	5.88	5	40	1	2	−2.0	2.5	95
BZX79C6V2RL	79C6V2	5.89	6.2	6.51	5	10	3	4	0.4	3.7	90
BZX79C6V8RL	79C6V8	6.46	6.8	7.19	5	15	2	4	1.2	4.5	85
BZX79C7V5RL	79C7V5	7.13	7.5	7.88	5	15	1	5	2.5	5.3	80
BZX79C8V2RL	79C8V2	7.79	8.2	8.61	5	15	0.7	5	3.2	6.2	75
BZX79C10RL	79C10	9.5	10	10.5	5	20	0.2	7	4.5	8.0	70
BZX79C12RL	79C12	11.4	12	12.6	5	25	0.1	8	6.0	10	65
BZX79C15RL	79C15	14.25	15	15.75	5	30	0.05	10.5	9.2	13	55
BZX79C16RL	79C16	15.2	16	16.8	5	40	0.05	11.2	10.4	14	52
BZX79C18RL	79C18	17.1	18	18.9	5	45	0.05	12.6	12.9	16	47
BZX79C22RL	79C22	20.9	22	23.1	5	55	0.05	15.4	16.4	20	34
BZX79C24RL	79C24	22.8	24	25.2	5	70	0.05	16.8	18.4	22	33
BZX79C27RL	79C27	25.65	27	28.35	5	80	0.05	18.9	—	23.5	30
BZX79C30RL	79C30	28.5	30	31.5	5	80	0.05	21	—	26	27
BZX79C33RL	79C33	31.35	33	34.65	5	80	0.05	23.1	—	29	25

2. TOLERANCE AND VOLTAGE DESIGNATION

Tolerance designation – the type numbers listed have zener voltage min/max limits as shown.

3. REVERSE ZENER VOLTAGE (V_Z) MEASUREMENT

Reverse zener voltage is measured under pulse conditions such that T_J is no more than 2°C above T_A .

4. ZENER IMPEDANCE (Z_Z) DERIVATION

Z_{ZT} and Z_{ZK} are measured by dividing the ac voltage drop across the device by the ac current applied. The specified limits are for $I_{Z(ac)} = 0.1 I_{Z(dc)}$ with the ac frequency = 1.0 kHz.

BZX79C2V4RL Series

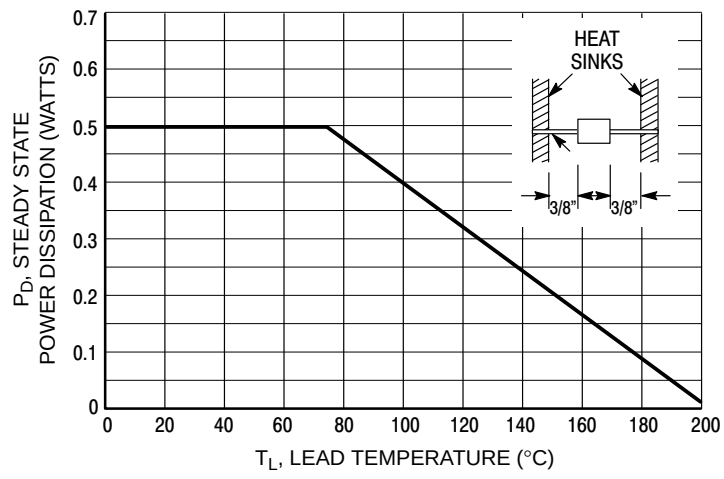


Figure 1. Steady State Power Derating

APPLICATION NOTE — ZENER VOLTAGE

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Lead Temperature, T_L , should be determined from:

$$T_L = \theta_{LA} P_D + T_A.$$

θ_{LA} is the lead-to-ambient thermal resistance ($^{\circ}\text{C}/\text{W}$) and P_D is the power dissipation. The value for θ_{LA} will vary and depends on the device mounting method. θ_{LA} is generally 30 to $40^{\circ}\text{C}/\text{W}$ for the various clips and tie points in common use and for printed circuit board wiring.

The temperature of the lead can also be measured using a thermocouple placed on the lead as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_L , the junction temperature may be determined by:

$$T_J = T_L + \Delta T_{JL}.$$

ΔT_{JL} is the increase in junction temperature above the lead temperature and may be found from Figure 2 for dc power:

$$\Delta T_{JL} = \theta_{JL} P_D.$$

For worst-case design, using expected limits of I_Z , limits of P_D and the extremes of $T_J(\Delta T_J)$ may be estimated. Changes in voltage, V_Z , can then be found from:

$$\Delta V = \theta_{VZ} T_J.$$

θ_{VZ} , the zener voltage temperature coefficient, is found from Figures 4 and 5.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

Surge limitations are given in Figure 7. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots, resulting in device degradation should the limits of Figure 7 be exceeded.

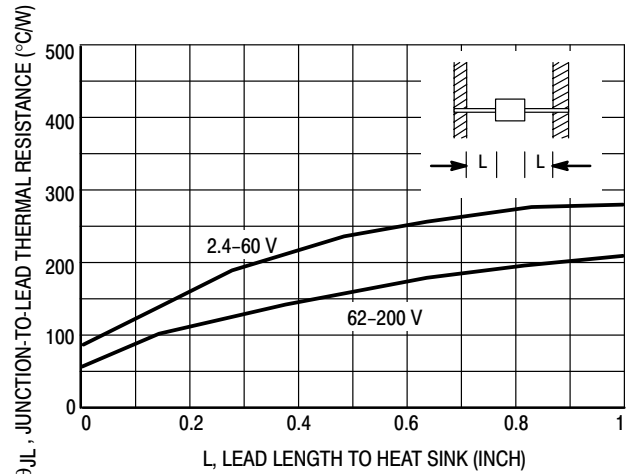


Figure 2. Typical Thermal Resistance

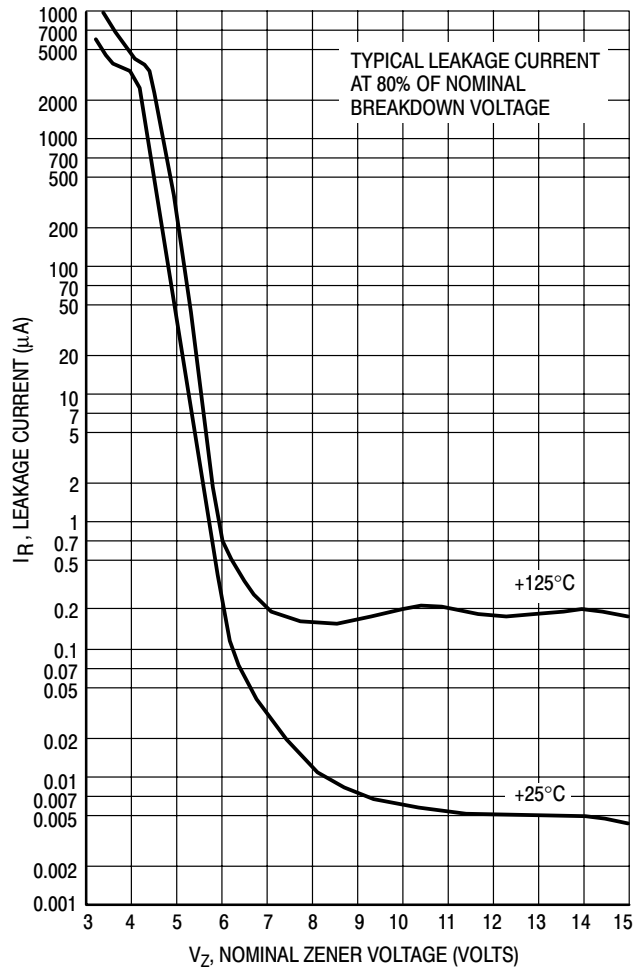


Figure 3. Typical Leakage Current

BZX79C2V4RL Series

TEMPERATURE COEFFICIENTS

(-55°C to +150°C temperature range; 90% of the units are in the ranges indicated.)

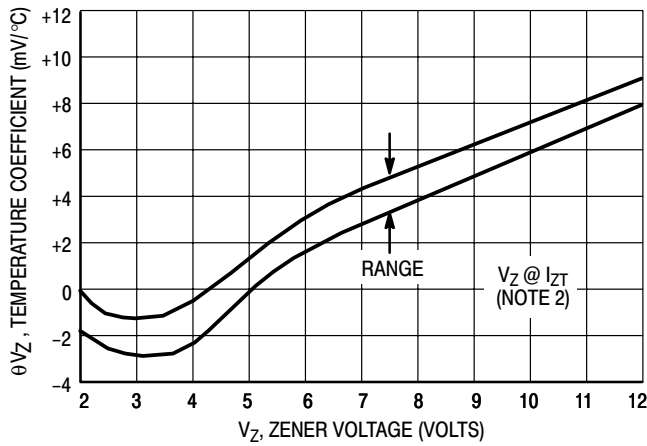


Figure 4a. Range for Units to 12 Volts

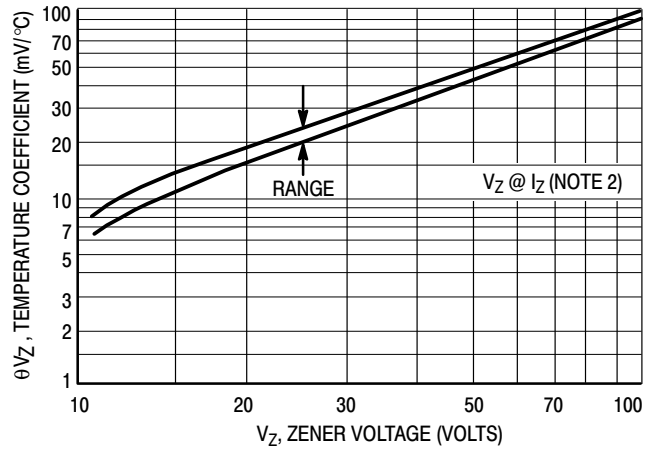


Figure 4b. Range for Units 12 to 100 Volts

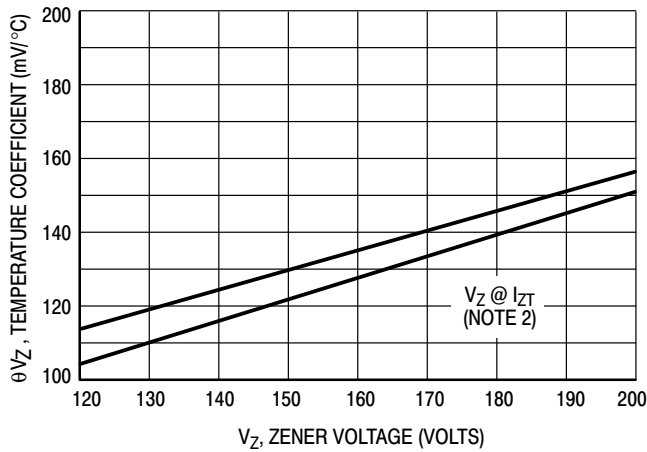


Figure 4c. Range for Units 120 to 200 Volts

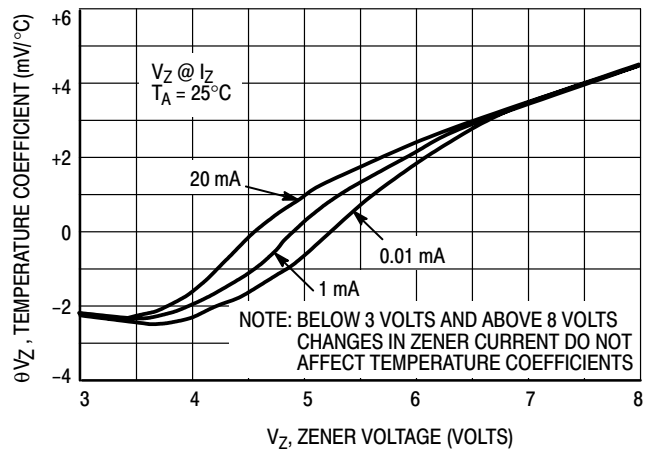


Figure 5. Effect of Zener Current

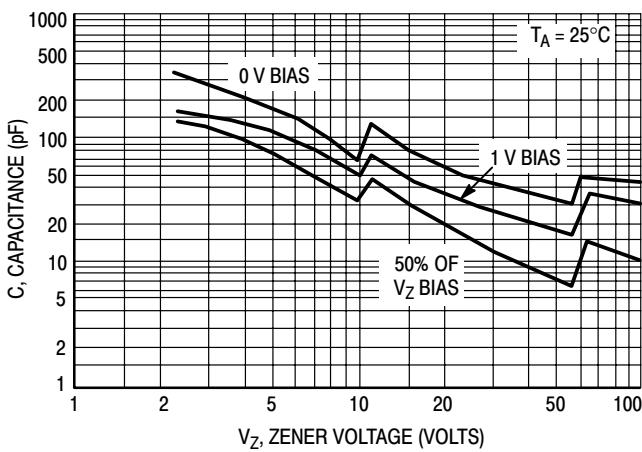


Figure 6a. Typical Capacitance 2.4–100 Volts

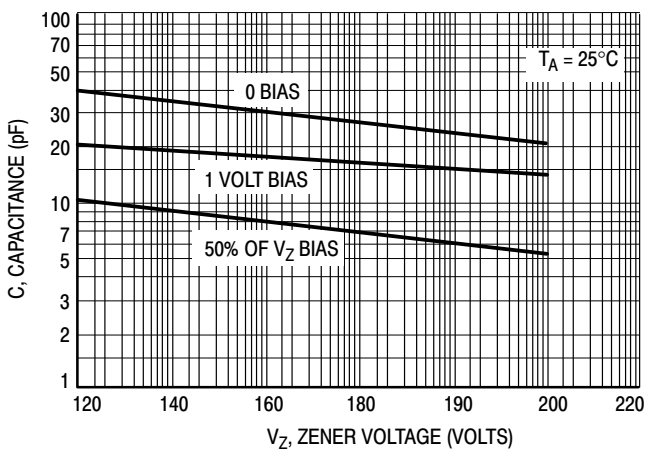


Figure 6b. Typical Capacitance 120–200 Volts

BZX79C2V4RL Series

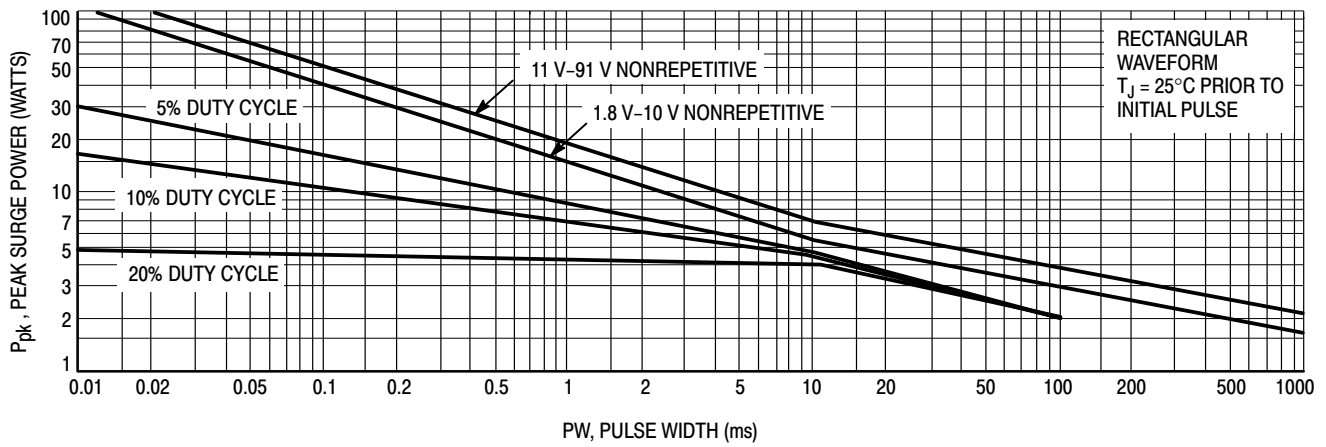


Figure 7a. Maximum Surge Power 1.8-91 Volts

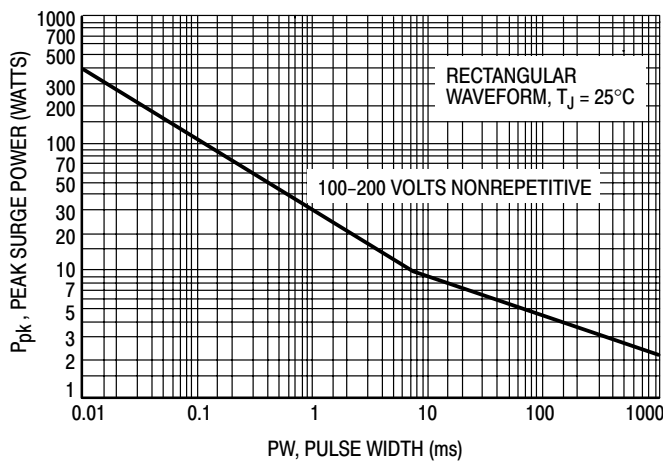


Figure 7b. Maximum Surge Power DO-204AH
100-200 Volts

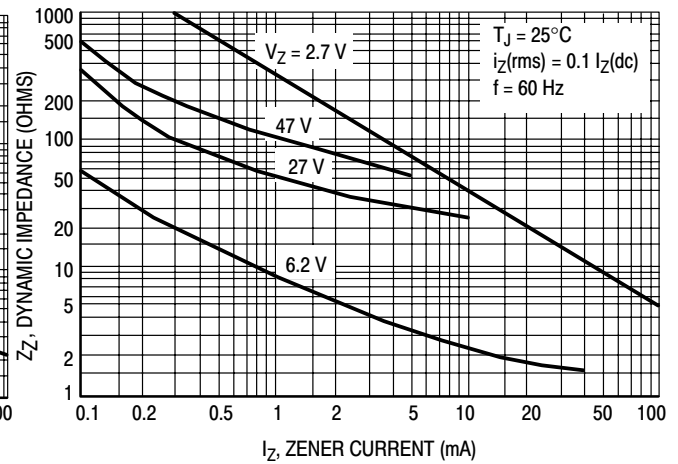


Figure 8. Effect of Zener Current on
Zener Impedance

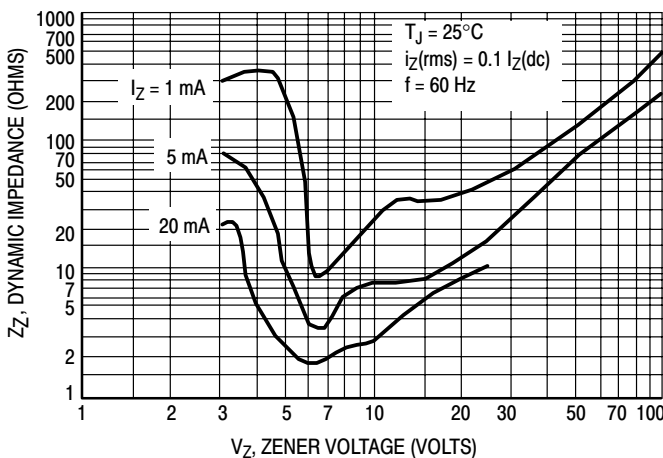


Figure 9. Effect of Zener Voltage on Zener Impedance

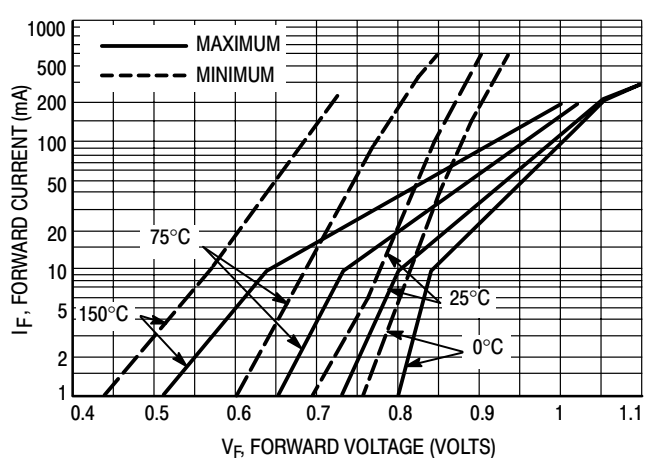


Figure 10. Typical Forward Characteristics

BZX79C2V4RL Series

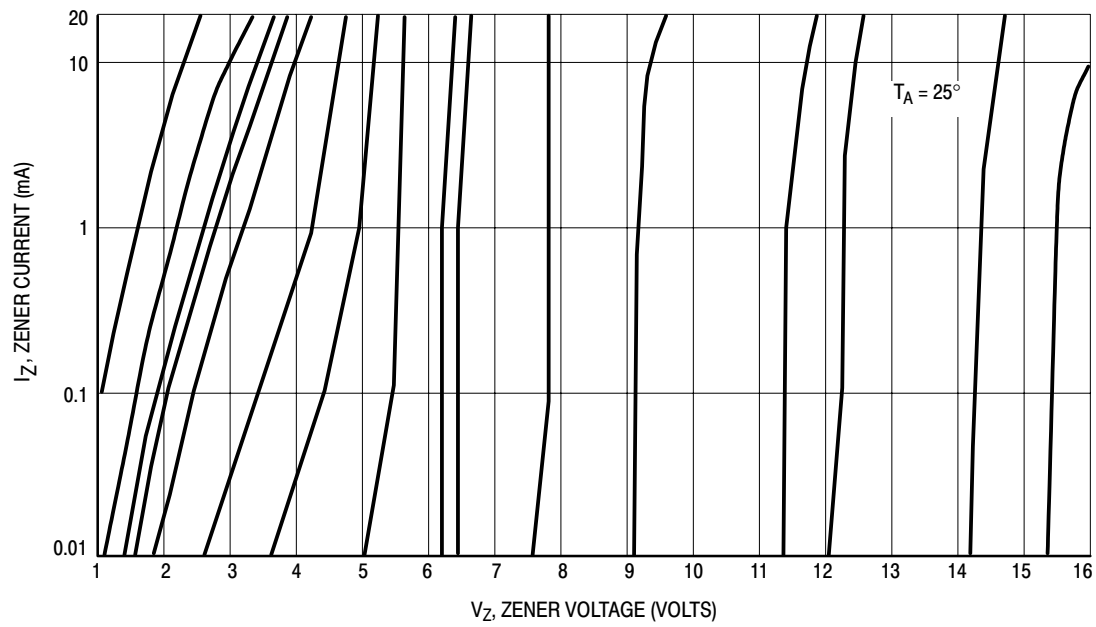


Figure 11. Zener Voltage versus Zener Current — $V_Z = 1$ thru 16 Volts

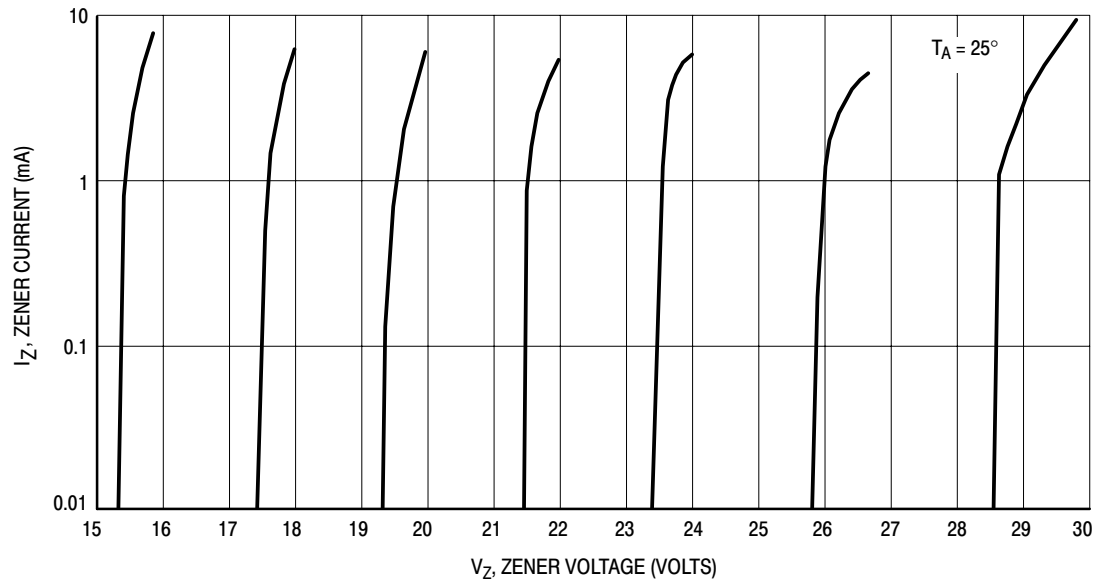


Figure 12. Zener Voltage versus Zener Current — $V_Z = 15$ thru 30 Volts

BZX79C2V4RL Series

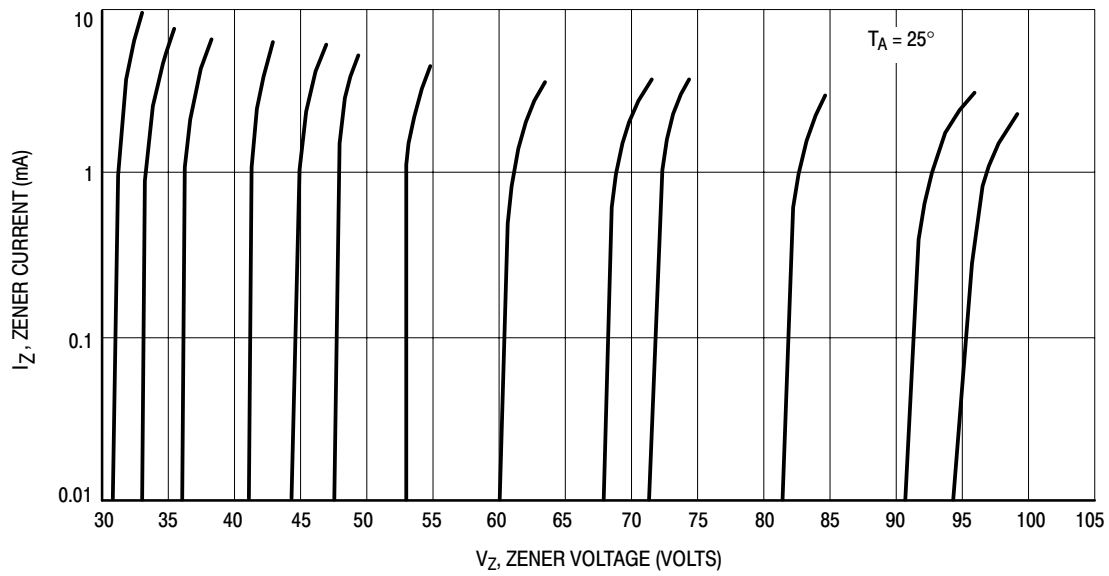


Figure 13. Zener Voltage versus Zener Current — $V_Z = 30$ thru 105 Volts

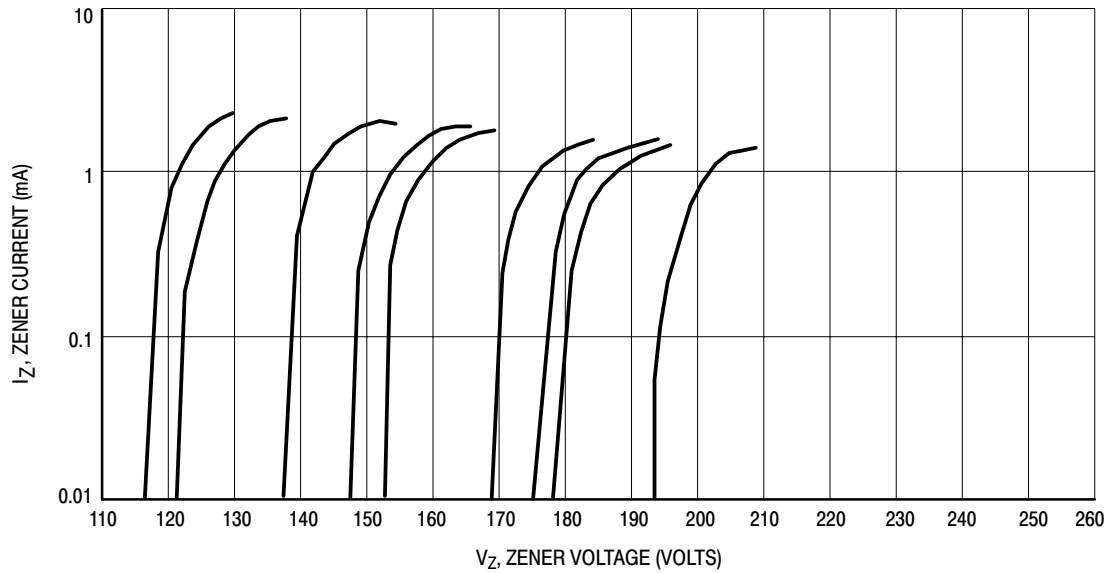
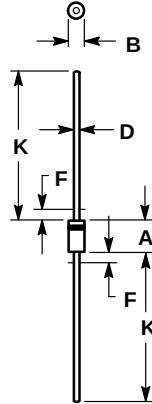


Figure 14. Zener Voltage versus Zener Current — $V_Z = 110$ thru 220 Volts

Zener Voltage Regulators – Axial Leaded

500 mW DO–35 Glass

GLASS DO–35/D0–204AH
CASE 299–02
ISSUE A



NOTES:

1. PACKAGE CONTOUR OPTIONAL WITHIN A AND B HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT NOT SUBJECT TO THE MINIMUM LIMIT OF B.
2. LEAD DIAMETER NOT CONTROLLED IN ZONE F TO ALLOW FOR FLASH, LEAD FINISH BUILDUP AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.
3. POLARITY DENOTED BY CATHODE BAND.
4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	3.05	5.08	0.120	0.200
B	1.52	2.29	0.060	0.090
D	0.46	0.56	0.018	0.022
F	---	1.27	---	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply.

Notes

Notes

BZX79C2V4RL Series

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

NORTH AMERICA Literature Fulfillment:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: ONlit@hibbertco.com
Fax Response Line: 303-675-2167 or 800-344-3810 Toll Free USA/Canada

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

EUROPE: LDC for ON Semiconductor – European Support

German Phone: (+1) 303-308-7140 (Mon-Fri 2:30pm to 7:00pm CET)
Email: ONlit-german@hibbertco.com
French Phone: (+1) 303-308-7141 (Mon-Fri 2:00pm to 7:00pm CET)
Email: ONlit-french@hibbertco.com
English Phone: (+1) 303-308-7142 (Mon-Fri 12:00pm to 5:00pm GMT)
Email: ONlit@hibbertco.com

EUROPEAN TOLL-FREE ACCESS*: 00-800-4422-3781

*Available from Germany, France, Italy, UK, Ireland

CENTRAL/SOUTH AMERICA:

Spanish Phone: 303-308-7143 (Mon-Fri 8:00am to 5:00pm MST)
Email: ONlit-spanish@hibbertco.com
Toll-Free from Mexico: Dial 01-800-288-2872 for Access –
then Dial 866-297-9322

ASIA/PACIFIC: LDC for ON Semiconductor – Asia Support

Phone: 1-303-675-2121 (Tue-Fri 9:00am to 1:00pm, Hong Kong Time)
Toll Free from Hong Kong & Singapore:
001-800-4422-3781
Email: ONlit-asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center

4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031
Phone: 81-3-5740-2700
Email: r14525@onsemi.com

ON Semiconductor Website: <http://onsemi.com>

For additional information, please contact your local Sales Representative.